

deposited on the first insulating layer 117 in succession to form switch and sensor active layers 121 and 119, and switch and sensor ohmic contact layers 125 and 123 over switch and sensor gates 115 and 111, respectively. Switch and sensor active layers 121 and 119 are preferably smaller than the switch and sensor gates 115 and 111, respectively, in order to protect the active layers 121 and 119 from the light of a light source (not shown) under the substrate 110. A transparent conducting material is deposited thereon to form switch source and drain electrodes 129a and 129b, a second capacitor electrode 131 and sensor source and drain electrodes 127a and 127b. In the thin film transistor optical detecting sensor, since it is desirable that light from the light source positioned under the substrate 110 should be transmitted to an object over the substrate through the substrate 110, especially through the window area "H" as much as possible, a transparent conducting material such as indium tin oxide is used.

IN THE CLAIMS

Please WITHDRAW claims 5-8, 11, and 12 from consideration and without prejudice.

Please AMEND claims 1, 9, and 10 as follows (Exhibit II is a marked up version of the

claim changes):

1. (Amended) An optical detecting sensor, comprising:

a sensor thin film transistor (TFT) generating optical current by incident light reflected

from an object;

a storage capacitor storing charges of the optical current generated in the sensor thin film

transistor;